

Number	Hits Search Text	DB	Time stamp
3219	((438/778) or (438/763)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 15:15
115	((438/778) or (438/763)).CCLS.) and ((Silicon near carbide) or SiC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 13:57
54	((438/778) or (438/763)).CCLS.) and (((Silicon near carbide) or SiC) same substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:06
7	((("4788082") or ("5562952") or ("5597744") or ("5614749") or ("5656516") or ("5789311") or ("5796122"))).PN.	USPAT	2002/10/17 14:11
756	((silicon near carbide) or SiC) near substrate) and (silicon same (oxidizing or oxidized or oxide or oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:16
8	(((((silicon near carbide) or SiC) near substrate) and (silicon same (oxidizing or oxidized or oxide or oxidation))) and (H2O or water same (partial near pressure)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:37
3	((("5648282") or ("5972801") or ("6017809"))).PN.	USPAT	2002/10/17 14:39
8437	((438/767) or (438/770) or (438/931) or (438/305) or (438/585) or (438/763) or (438/706) or (438/773) or (438/787) or (438/765) or (257/77)).CCLS.	USPAT; US-PGPUB; EPO; JPO	2002/10/17 14:40
881	((438/767) or (438/770) or (438/931) or (438/305) or (438/585) or (438/763) or (438/706) or (438/773) or (438/787) or (438/765) or (257/77)).CCLS.) and (SiC or (silicon near carbide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:44
208	((438/767) or (438/770) or (438/931) or (438/305) or (438/585) or (438/763) or (438/706) or (438/773) or (438/787) or (438/765) or (257/77)).CCLS.) and (SiC or (silicon near carbide))) and (silicon near (layer or film)) same (oxide or oxidation or oxidize or oxidized or oxidized)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:46
2	(SiC adj substrate) and (STI)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:57
996	(STI and (silicon near oxidation))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:57
0	((STI and (silicon near oxidation))) and (silicon near carbide) near substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:58
33	((STI and (silicon near oxidation))) and (silicon near carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/17 14:58

-	1248 SiC adj substrate	USPAT;	2002/10/17
		US-PGPUB;	15:19
		EPC; JPC;	
		DERWENT;	
		IBM_TDB	
-	0 (SiC adj substrate) and (STI same silicon)	USPAT;	2002/10/17
		US-PGPUB;	15:19
		EPC; JPC;	
		DERWENT;	
		IBM_TDB	
-	234 (432/205).CCLS.	USPAT;	2002/10/17
		US-PGPUB;	15:45
		EPC; JPC;	
		DERWENT;	
		IBM_TDB	
-	1 ((432/205).CCLS.) and (SiC near substrate)	USPAT;	2002/10/17
		US-PGPUB;	15:51
		EPC; JPC;	
		DERWENT;	
		IBM_TDB	
-	25 (SiC adj substrate) and (pure near water)	USPAT;	2002/10/17
		US-PGPUB;	15:52
		EPC; JPC;	
		DERWENT;	
		IBM_TDB	